

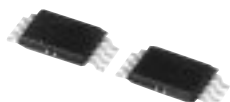
PRELIMINARY
 Notice: This is not a final specification.
 Some parametric limits are subject to change.

MITSUBISHI Nch POWER MOSFET

FY6BCH-02E

HIGH-SPEED SWITCHING USE

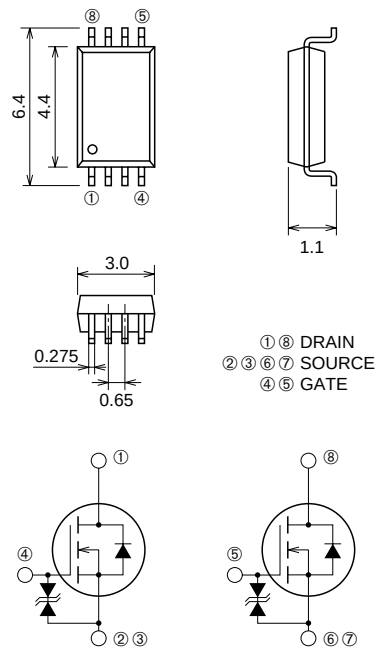
FY6BCH-02E



- 2.5V DRIVE
- V_{DS} 20V
- $r_{DS(ON)}$ (MAX) 30m Ω
- I_D 6A

OUTLINE DRAWING

Dimensions in mm



TSSOP8

APPLICATION

Motor control, Lamp control, Solenoid control
 DC-DC converter, etc.

MAXIMUM RATINGS (T_c = 25°C)

Symbol	Parameter	Conditions	Ratings	Unit
V_{DS}	Drain-source voltage	$V_{GS} = 0V$	20	V
V_{GSS}	Gate-source voltage	$V_{DS} = 0V$	±10	V
I_D	Drain current		6	A
I_{DM}	Drain current (Pulsed)		42	A
I_{DA}	Avalanche drain current (Pulsed)	$L = 10\mu H$	6	A
I_S	Source current		1.5	A
I_{SM}	Source current (Pulsed)		6.0	A
P_D	Maximum power dissipation		1.5	W
T_{ch}	Channel temperature		-55 ~ +150	°C
T_{stg}	Storage temperature		-55 ~ +150	°C
—	Weight	Typical value	0.035	g

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ELECTRICAL CHARACTERISTICS (Tch = 25°C)

Symbol	Parameter	Test conditions	Limits			Unit
			Min.	Typ.	Max.	
V (BR) DSS	Drain-source breakdown voltage	Id = 1mA, VGS = 0V	20	—	—	V
V (BR) GSS	Gate-source breakdown voltage	IG = ±100μA, VDS = 0V	±10	—	—	V
IGSS	Gate-source leakage current	VGS = ±10V, VDS = 0V	—	—	±10	μA
IDSS	Drain-source leakage current	VDS = 20V, VGS = 0V	—	—	0.1	mA
VGS (th)	Gate-source threshold voltage	Id = 1mA, VDS = 10V	0.5	0.9	1.3	V
rDS (ON)	Drain-source on-state resistance	Id = 6A, VGS = 4V	—	25	30	mΩ
rDS (ON)	Drain-source on-state resistance	Id = 3A, VGS = 2.5V	—	34	45	mΩ
VDS (ON)	Drain-source on-state voltage	Id = 6A, VGS = 4V	—	0.15	0.18	V
yfs	Forward transfer admittance	Id = 6A, VDS = 10V	—	14	—	S
Ciss	Input capacitance	VDS = 10V, VGS = 0V, f = 1MHz	—	900	—	pF
Coss	Output capacitance		—	330	—	pF
Crss	Reverse transfer capacitance		—	240	—	pF
td (on)	Turn-on delay time	VDD = 10V, Id = 3A, VGS = 4V, RGEN = RGS = 50Ω	—	20	—	ns
tr	Rise time		—	55	—	ns
td (off)	Turn-off delay time		—	105	—	ns
tf	Fall time		—	115	—	ns
VSD	Source-drain voltage	IS = 1.5A, VGS = 0V	—	—	1.10	V
Rth (ch-a)	Thermal resistance	Channel to ambient	—	—	83.3	°C/W
trr	Reverse recovery time	IS = 1.5A, dis/dt = -50A/μs	—	50	—	ns